

PSMN8R5-60YS

N-channel LFPAK 60 V, 8 mΩ standard level MOSFET

22 July 2015

Product data sheet

1. General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

3. Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Motor control
- Server power supplies

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|------|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | - | 60 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u> | - | - | 76 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | - | 106 | W |
| Tj | junction temperature | | -55 | - | 175 | °C |
| Static charact | eristics | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ Fig. 12 | - | - | 12.8 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 13 | - | 5.6 | 8 | mΩ |
| Dynamic char | acteristics | | | | | |
| Q_{GD} | gate-drain charge | V _{GS} = 10 V; I _D = 60 A; V _{DS} = 30 V; Fig. 15; Fig. 14 | - | 7.7 | - | nC |



| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---|--|-----|-----|-----|------|
| Q _{G(tot)} | total gate charge | $V_{GS} = 10 \text{ V}; I_D = 60 \text{ A}; V_{DS} = 30 \text{ V};$ Fig. 14; Fig. 15 | - | 39 | - | nC |
| Avalanche rug | gedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 76 A; $V_{sup} \le$ 60 V; R_{GS} = 50 Ω ; unclamped | - | - | 97 | mJ |

Pinning information

Table 2. **Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--|----------------|
| 1 | S | source | mb | D I |
| 2 | S | source | | |
| 3 | S | source | [q] | G UNA |
| 4 | G | gate | وققق | mbb076 S |
| mb | D | mounting base; connected to drain | 1 2 3 4 LFPAK56; Power- SO8 (SOT669) | |

Ordering information

Table 3. **Ordering information**

| Type number | Package | | | | |
|--------------|-----------------------|--|---------|--|--|
| | Name | Description | Version | | |
| PSMN8R5-60YS | LFPAK56; Power-SO8 | Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads | SOT669 | | |

Marking 7.

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| PSMN8R5-60YS | 8R560 |

Limiting values 8.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|----------------------|--|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 60 | V |
| V_{DGR} | drain-gate voltage | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$ | - | 60 | V |

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| Symbol | Parameter | Conditions | Min | Max | Unit |
|----------------------|--|--|-----|-----|------|
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | 106 | W |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u> | - | 54 | Α |
| | | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | - | 76 | Α |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3 | - | 303 | Α |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| $T_{sld(M)}$ | peak soldering temperature | | - | 260 | °C |
| Source-drai | n diode | | | | |
| I _S | source current | T _{mb} = 25 °C | - | 76 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | - | 303 | Α |
| Avalanche r | ruggedness | | 1 | | , |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 76 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; unclamped | - | 97 | mJ |

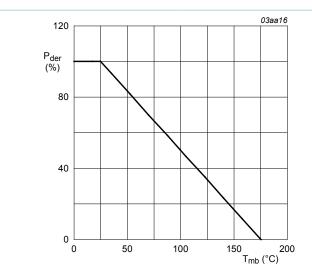


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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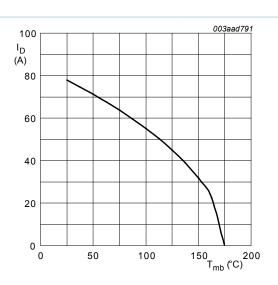


Fig. 2. Continuous drain current as a function of mounting base temperature



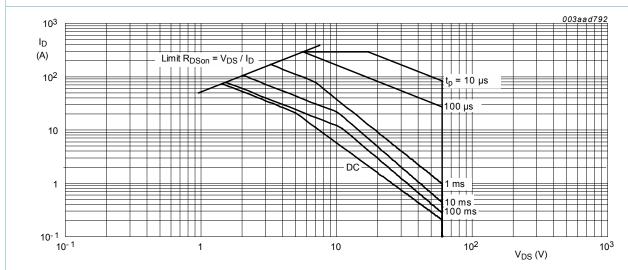


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$ °C; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|------------|-----|------|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 4 | - | 0.63 | 1.42 | K/W |

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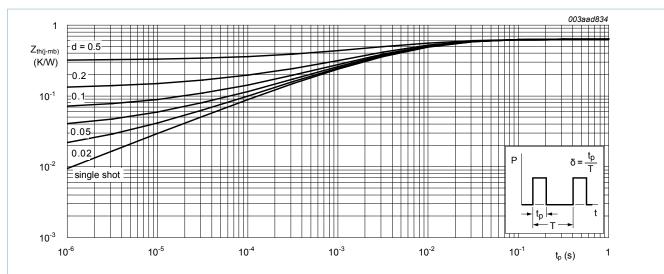


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--|---|--|-----|------|------|------|
| Static chara | acteristics | | | ' | | |
| V _{(BR)DSS} | drain-source | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ | 54 | - | - | V |
| | breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 60 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11 | 2 | 3 | 3.8 | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 11 | - | - | 4.3 | V |
| | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 11 | 0.95 | - | - | V | |
| I _{DSS} drain leakage current | drain leakage current | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 0.03 | 2 | μA |
| | V _{DS} = 60 V; V _{GS} = 0 V; T _j = 125 °C | - | - | 50 | μA | |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I_D = 15 A; T_j = 175 °C; Fig. 12 | - | 12 | 18.4 | mΩ |
| | | V_{GS} = 10 V; I_D = 15 A; T_j = 100 °C; Fig. 12 | - | - | 12.8 | mΩ |
| | | V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; Fig. 13 | - | 5.6 | 8 | mΩ |
| R _G | gate resistance | f = 1 MHz | - | 0.61 | - | Ω |

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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|---------------------------------------|---|-----|------|-----|------|
| Dynamic ch | naracteristics | | l l | | | |
| Q _{G(tot)} | total gate charge | I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 14; Fig. 15 | - | 39 | - | nC |
| | | I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V | - | 33 | - | nC |
| Q_{GS} | gate-source charge | I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 15; Fig. 14 | - | 13.3 | - | nC |
| Q _{GS(th)} | pre-threshold gate- source charge | I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 14 | - | 7 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate- source charge | | - | 6.2 | - | nC |
| Q_{GD} | gate-drain charge | I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 15; Fig. 14 | - | 7.7 | - | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | V _{DS} = 30 V; <u>Fig. 14</u> ; <u>Fig. 15</u> | - | 5.2 | - | V |
| C _{iss} | input capacitance | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16$ | - | 2370 | - | pF |
| C _{oss} | output capacitance | | - | 307 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 172 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 30 V; R_L = 0.5 Ω ; V_{GS} = 10 V; | - | 18.4 | - | ns |
| t _r | rise time | $R_{G(ext)} = 4.7 \Omega$ | - | 13.7 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 32.4 | - | ns |
| t _f | fall time | | - | 9.2 | - | ns |
| Source-dra | in diode | | ı | | | |
| V _{SD} | source-drain voltage | I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u> | - | 0.8 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 20 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ | - | 43.3 | - | ns |
| Q _r | recovered charge | V _{DS} = 30 V | - | 61.4 | - | nC |

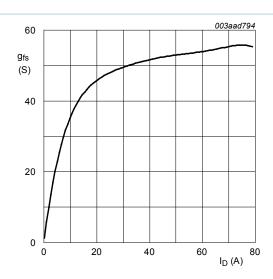


Fig. 5. Forward transconductance as a function of drain current; typical values

$$T_j = 25$$
 °C; $V_{DS} = 20$ V

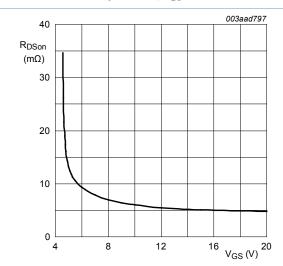


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
 °C; $I_D = 20$ A

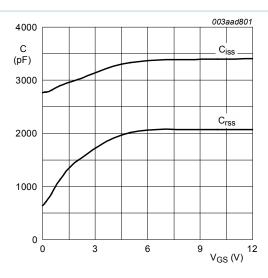


Fig. 6. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

$$V_{DS} = 0 \text{ V; } f = 1 \text{ MHz}$$

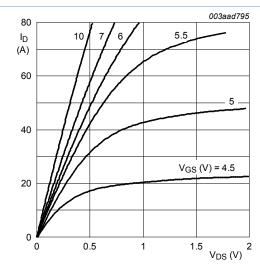


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25 \,^{\circ}C$$

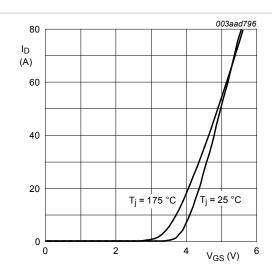


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



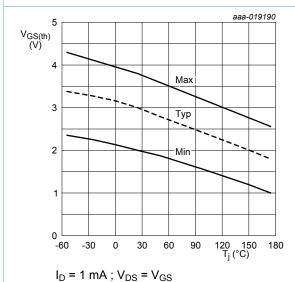
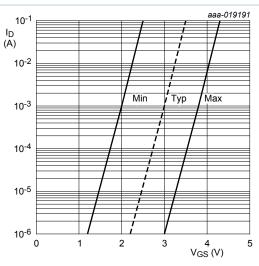


Fig. 11. Gate-source threshold voltage as a function of junction temperature



$$T_i = 25 \,^{\circ}C; V_{DS} = 5V$$

Fig. 10. Sub-threshold drain current as a function of gate-source voltage

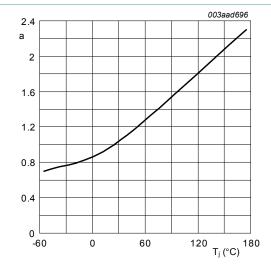


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

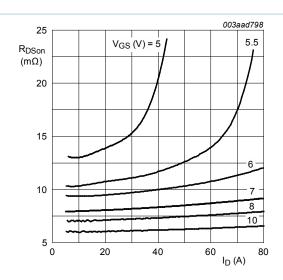


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

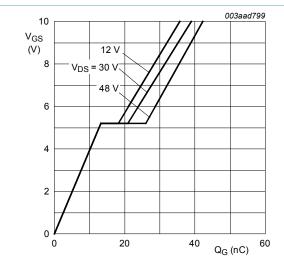


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
 °C; $I_D = 60$ A

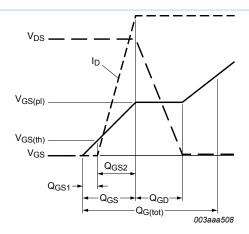


Fig. 14. Gate charge waveform definitions

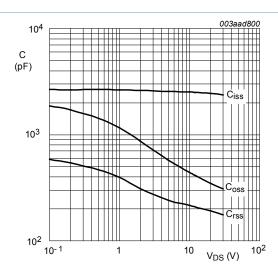


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

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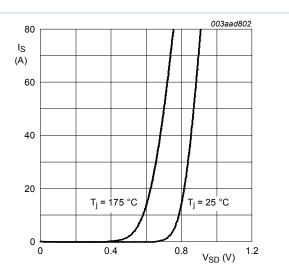


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline

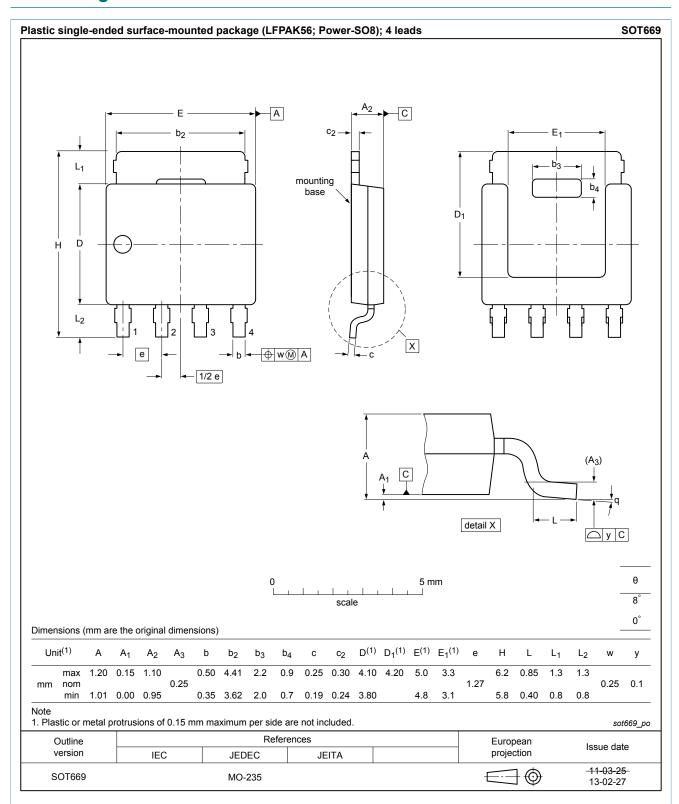


Fig. 18. Package outline LFPAK56; Power-SO8 (SOT669)

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